Product data sheet

1. General description

Dual ultrafast power diode in a TO220 package.

2. Features and benefits

- Ultra low leakage current
- High junction temperature up to 175 °C
- Low on-state loss
- Fast switching
- · Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- · High thermal cycling performance
- · Low thermal resistance

3. Applications

- Home appliance power supply
- Secondary rectification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		300				V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 159 °C; per diode; Fig. 1; Fig. 2; Fig. 3	10				А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 159 °C; square-wave pulse; per diode	20				А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	220				А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	242			А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	-	1.25	V
		I _F = 10 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	-	1	V
Dynamic	characteristics		1	1	1		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/µs}$; $T_j = 25 \text{ °C}$; per diode; Fig. 7		-	-	25	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		A1
3	A2	anode		<u> </u>
mb	K	mounting base; connected to cathode		sym125

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYV32E-300P	TO220	BYV32E-300PQ	Tube	50	TO220E	26-May-2017

7. Marking

Table 4. Marking codes

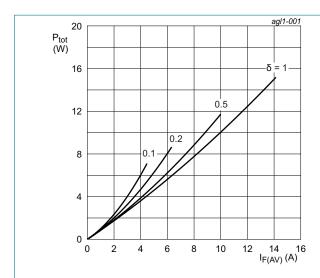
Type number	Marking codes
BYV32E-300P	BYV32E-300P

8. Limiting values

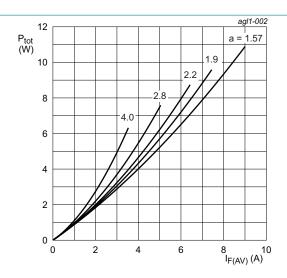
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		300	V
V_{RWM}	crest working reverse voltage		300	V
V_R	reverse voltage	DC	300	V
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 159$ °C; per diode; Fig. 1; Fig. 2; Fig. 3	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 159 °C; square-wave pulse; per diode	20	А
$I_{\text{O(AV)}}$	average output current	δ = 0.5 ; T _{mb} ≤ 157 °C; square-wave pulse; both diodes conducting	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	220	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	242	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} & |_{\text{F(AV)}} = |_{\text{F(RMS)}} \times \sqrt{\delta} \\ & |_{\text{V}_{\text{o}}} = 0.836 \text{ V}; \text{ R}_{\text{s}} = 0.0168 \text{ }\Omega \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.836 V; R_s = 0.0168 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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Dual ultrafast power diode

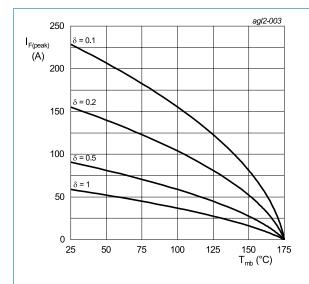


Fig. 3. Forward current as a function of mounting base temperature; maximum values; per diode

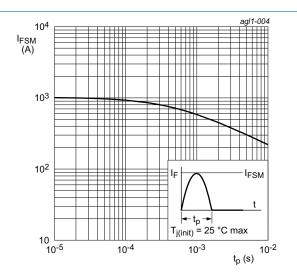


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	1.4	K/W
	mounting base	with heatsink compound; both diodes conducting; Fig. 5	-	-	0.75	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

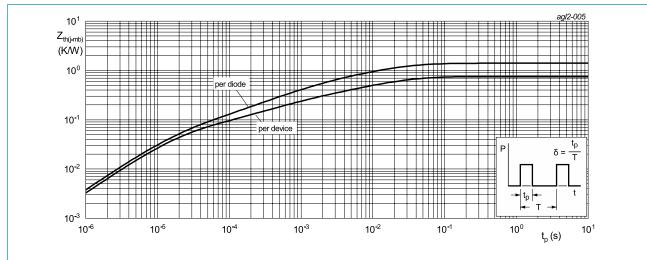
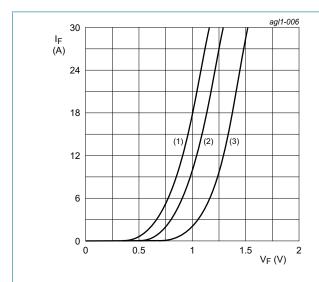


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V_{F}	forward current	I _F = 10 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	-	1.25	V
		I _F = 10 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	-	1	V
I _R	reverse current	V _R = 300 V; T _j = 25 °C; per diode	-	-	20	μA
		V _R = 300 V; T _j = 125 °C; per diode	-	-	300	μA
Dynamic	characteristics					
Q _r	reverse charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$	-	9	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; per diode; Fig. 7	-	-	35	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$	-	-	25	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$	-	25	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; per diode; Fig. 7$	-	33	-	ns
I _{RM}	peak reverse recovery current	I_F = 1 A; V_R = 30 V; dI_F/dt = 50 A/ μ s; T_j = 25 °C; per diode; Fig. 7	-	0.7	-	А
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; per diode; Fig. 7$	-	1.1	-	А
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s}; T_j = 25 °C; per diode; Fig. 7$	-	2.8	-	А
		$I_F = 10 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/µs}$; $T_i = 125 \text{ °C}$; per diode; Fig. 7	-	-	8	А



 $V_o = 0.836 \text{ V}; R_s = 0.0168 \Omega$

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

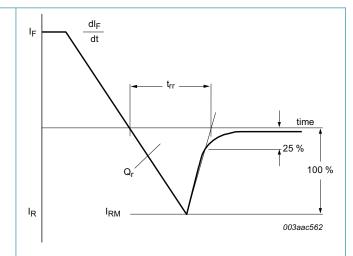
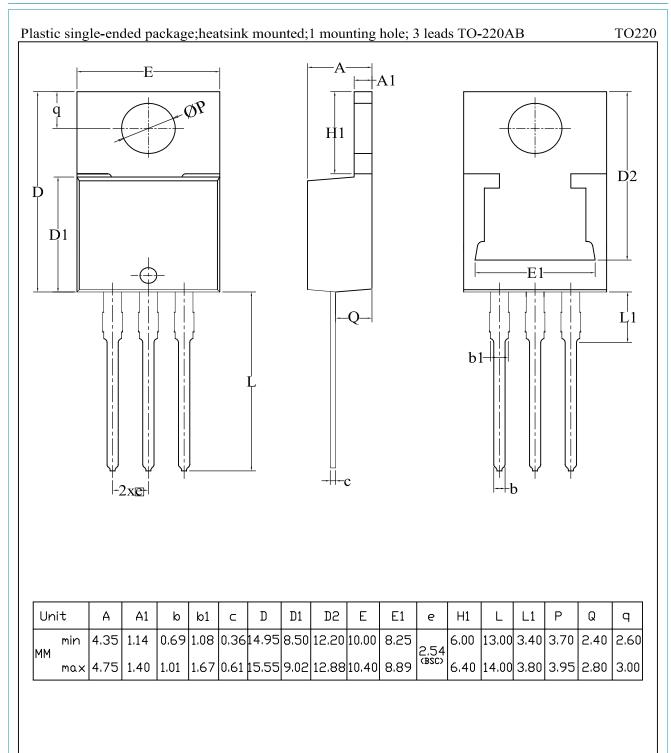


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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